

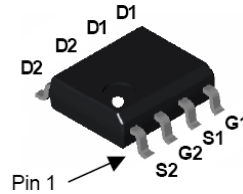
P-Channel MOSFET AO4953

General Description

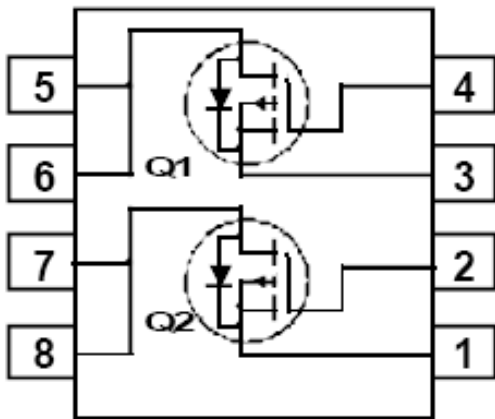
AO4953 SG Series Dual P-channel enhancement mode field-effect transistor ,produced with high cell density DMOS trench technology, which is especially used to minimize on-state resistance. This device particularly suits low voltage applications, and low power dissipation .

Features

- -30V/-6A
 $R_{DS(ON)} = 52m\Omega @ V_{GS} = -10V, I_D = -6A$
 $R_{DS(ON)} = 67m\Omega @ V_{GS} = -4.5V, I_D = -4A$
- High Density Cell Design For Ultra Low On-Resistance
- Surface mount package:SOP8



Pin Configuration



Typical Application

- Power management
- Load switch
- Battery protection

Absolute Maximum Ratings

Parameter		Symbol	Ratings	Unit
Drain-Source Voltage		V_{DSS}	-30V	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	$T_A = 25^\circ C$	I_D	-6	A
	$T_A = 70^\circ C$		-4	
Pulsed Drain Current ^{1,2}		I_{DM}	-30	A
Total Power Dissipation	$T_A = 25^\circ C$	P_d	1.3	W
	$T_A = 70^\circ C$		0.8	
Operating Temperature Range		T_{Opr}	150	$^\circ C$
Storage Temperature Range		T_{stg}	-65/150	$^\circ C$